

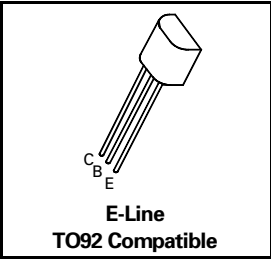
NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTORS

2N6724 2N6725

ISSUE 1 – MARCH 94

FEATURES

- * 50 Volt V_{CEO}
- * Gain of 15k at $I_C = 0.5$ Amp
- * $P_{tot} = 1$ Watt



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	2N6724	2N6725	UNIT
Collector-Base Voltage	V_{CBO}	50	60	V
Collector-Emitter Voltage	V_{CEO}	40	50	V
Emitter-Base Voltage	V_{EBO}	10		V
Peak Pulse Current	I_{CM}	2		A
Continuous Collector Current	I_C	1		A
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	1		W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	2N6724		2N6725		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50		60		V	$I_C = 1\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40		50		V	$I_C = 1\text{mA}, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10		10		V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cut-Off Current	I_{CBO}		1.0		1.0	μA μA	$V_{CB} = 30\text{V}, I_E = 0$ $V_{CB} = 40\text{V}, I_E = 0$
Emitter Cut-Off Current	I_{EBO}		0.1		0.1	μA	$V_{EB} = 8\text{V}, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		1.0		1.0	V	$I_C = 200\text{mA}, I_B = 2\text{mA}^*$ $I_C = 1\text{A}, I_B = 2\text{mA}^*$
			1.5		1.5	V	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		2.0		2.0	V	$I_C = 1\text{A}, I_B = 2\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		2.0		2.0	V	$I_C = 1\text{A}, V_{CE} = 5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	25K		25K			$I_C = 200\text{mA}, V_{CE} = 5\text{V}^*$ $I_C = 500\text{mA}, V_{CE} = 5\text{V}^*$ $I_C = 1\text{A}, V_{CE} = 5\text{V}^*$
		15K		15K			
		4K	40K	4K	40K		
Collector Base Capacitance	C_{CB}		10		10	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$